D. Thin Film Process Technology 분과

Room D
1F / 107호

2015년 2월 12일(목) 13:10-14:40
[TD2-D] Oxide Semiconductor & 2D Dichalcogenide Thin-Film Transistor Technologies

TD2-D-1	**13:10-13:25**	**Device Characterizations on the Performance and Stabilities of InGaZnO Thin Film Transistors Fabricated on Flexible Polyethylene Naphthalate** Minji Park[1], Jun-Yong Bak[1], Min-Ki Ryu[2], Jong-Heon Yang[2], Gi Heon Kim[2], Sung-Min Yoon[1] [1]Kyung Hee University, [2]Electronics & Telecommunication Research Institute
TD2-D-2	**13:25-13:40**	**Fully-Transparent Nonvolatile Memory Thin-Film Transistors Using Organic/Inorganic Hybrid Gate-Stack with Double-Gate Configuration** Da-Bin Jeon and Sung-Min Yoon Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University
TD2-D-3	**13:40-13:55**	**Nonvolatile Memory Performances of Transparent Memory Thin-Film Transistors Using IGZO Channel and ZnO Charge-Trap Layers** Sojung Kim, Jun-Yong Bak, and Sung-Min Yoon Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University
TD2-D-4	**13:55-14:10**	**Growth of MoS_2 Thin Films by Atomic Layer Deposition** Jung Joon Pyeon[1,2], Cheol Jin Cho[2,3], Soo Hyun Kim[1], Chong Yun Kang[1,2], and Seong Keun Kim[2] [1]KU-KIST Graduate school of Converging Science and Technology, [2]Electronic Material Center, Korea Institute of Science and Technology, [3]Department of Materials Science and Engineering and Interuniversity Semiconductor Research Center, Seoul National Unive
TD2-D-5	**14:10-14:25**	**Synthesis of Wafer-Scale Layer Controlled Molybdenum Disulfide using Atomic Layer Deposition** Youngjun Kim[1], Jeong-Gyu Song[1], GyeongHee Ryu[2], Sung-Hwan Hwang[3], Chang Wan Lee[1], Taejin Choi[1], Whang Je Woo[1], Hanearl Jung[1], Zonghoon Lee[2], Jae-Min Myoung[3], Jong-Hyun Ahn[1], Jusang Park[1], and Hyungjun Kim[1] [1]School of Electrical and Electronic Engineering, Yonsei University, [2]School of Materials Science and Engineering, Ulsan National Institute of Science and Technology (UNIST), [3]Department of Materials Science and Engineering, Yonsei University

TD2-D-6 **14:25-14:40** **MoS_2 전계효과 트랜지스터의 컨택 저항 개선 방법**

박우진, 김용훈, 이상경, 정욱진, 양진호, 조천흠, 김윤지, 임성관, 이병훈
Center for Emerging Electric Devices and Systems, School of Material Science and Engineering, Gwangju Institute of Science and Technology